

REJ03G1839-0100

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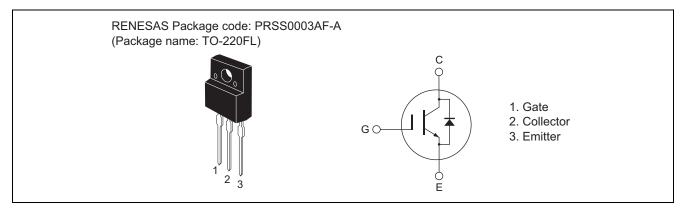
RJH60D1DPP-M0

Silicon N Channel IGBT Application: Inverter

Features

- High breakdown-voltage
- Low on-voltage
- Built-in diode

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

				(1a 25 C)	
Item		Symbol	Ratings	Unit	
Collector to emitter voltage / diode reverse voltage		V _{CES} / V _R	600	V	
Gate to emitter voltage		V _{GES}	±30	V	
Collector current	Tc = 25°C	lc	16	А	
	Tc = 100°C	lc	8	А	
Collector peak current		ic(peak) Note1	32	А	
Collector to emitter diode forward current		i _{DF}	8	А	
Collector to emitter diode forward peak current		i _D (peak) ^{Note1}	32	А	
Collector dissipation		P _C ^{Note2}	20	W	
Junction to case thermal impedance		θj-c ^{Note2}	6.25	°C/ W	
Junction temperature		Tj	150	۵°	
Storage temperature		Tstg	-55 to +150	С°	

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tc = 25°C

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

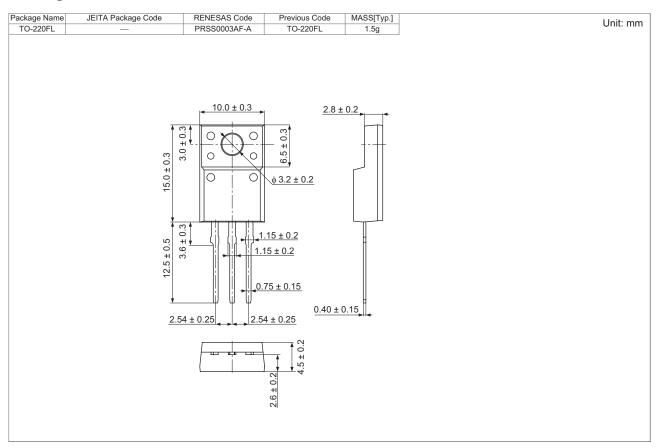
ltem	Symbol	Min	Тур	Max	Unit	Test Conditions	
Zero gate voltage collector current / Diode reverse current	I _{CES} / I _R	_	—	100	μΑ	V _{CE} = 600 V, V _{GE} = 0	
Gate to emitter leak current	I _{GES}			±1	μA	$V_{GE} = \pm 30 \text{ V}, \text{ V}_{CE} = 0$	
Gate to emitter cutoff voltage	V _{GE(off)}	4.0		6.0	V	V _{CE} = 10 V, I _C = 1 mA	
Collector to emitter saturation voltage	V _{CE(sat)}	_	1.8	2.2	V	$I_{\rm C}$ = 8 A, $V_{\rm GE}$ = 15 V ^{Note3}	
	V _{CE(sat)}	_	2.3		V	$I_{\rm C}$ =16 A, $V_{\rm GE}$ = 15 V ^{Note3}	
Input capacitance	Cies	_	290		pF	V _{CE} = 25 V	
Output capacitance	Coes	_	25		pF	V _{GE} = 0	
Reveres transfer capacitance	Cres	_	7.5		pF	f = 1 MHz	
Total gate charge	Qg	_	12.0	_	nC	V _{GE} = 15 V V _{CE} = 300 V	
Gate to emitter charge	Qge	_	2.0		nC		
Gate to collector charge	Qgc	_	6.0	_	nC	I _C = 8 A	
Switching time	t _{d(on)}	_	25		ns	I _C = 8 A	
	tr		35		ns	R _L = 37.5 Ω	
	t _{d(off)}	_	40		ns	V _{GE} = 15 V	
	t _f	_	100		ns	Rg = 5 Ω	

FRD Forward voltage	VF	_	1.8	2.3	V	I _F = 8 A ^{Note3}
FRD reverse recovery time	trr	—	100	—	ns	I _F = 8 A
						di _F /dt = 100 A/µs

Notes: 3. Pulse test.

4. Under development -The specifications potentially be changed without notice.

Package Dimension



Ordering Information

Part No.	Quantity	Shipping Container
RJH60D1DPP-M0-T2	1050 pcs	Box (Tube)

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